PNP EPITAXIAL SILICON DARLINGTON TRANSISTOR

DARLINGTON TRANSISTOR

Collector-Emitter Voltage: V_{CES}=KSP75: 40V
 KSP76: 50V
 KSP77: 60V

• Collector Dissipation: Pc (max)=625mW

ABSOLUTE MAXIMUM RATINGS (T_A=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage : KSP75 : KSP76 : KSP77 Emitter-Base Voltage Collector Current Collector Dissipation Junction Temperature Storage Temperature	V _{CES} V _{EBO} I _C P _C T _J T _{STG}	-40 -50 -60 -10 -500 625 150 -55~150	∨ ∨ v mA m ♥ ° °

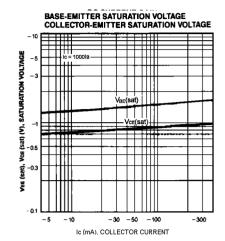


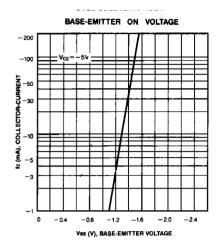
ELECTRICAL CHARACTERISTICS (T_A=25°C)

Characteristic		Symbol	Test Conditions	Min	Max	Unit
Collector-Base Breakdown V	oltage : KSP75	BV _{CEO}	I _C = -100μ A , I _B =0	-40		٧
	: KSP76 : KSP77			-50 -60		V V
Collector-Base Breakdown V	oltage : KSP75	ВV _{сво}	$I_{C}=-100\mu A, I_{E}=0$	-40		٧
	: KSP76 : KSP77			-50 -60		V V
Collector Cut-off Current	: KSP75	Ісво	V _{CE} = -30V, I _E =0		-100	n A
	: KSP76 : KSP77		$V_{CE} = -40V, I_{E} = 0$ $V_{CE} = -50V, I_{E} = 0$		-100 -100	n A n A
Emitter Cut-off Current Collector Cut-off Current		I _{EBO}	V _{CE} = -10V, I _B =0		-100	n A
	: KSP75 : KSP76		V _{CE} = -30V, I _E =0 V _{CE} = -40V, I _E =0 V _{CF} = -50V, I _F =0		-500 -500	n A n A
DC Current Gain	: KSP77	h _{FE}	V _{CE} = -50 V, I _E =0 V _{CE} = -5 V, I _C = -10 mA V _{CE} = -5 V, I _C = -100 mA	10K	-500	n A
		V _{CE} (sat) V _{BE} (on)	l _C = -100mA, l _B = -0.1mA V _{CE} = -5V, l _C = -100mA	10K	-1.5 -2	V V



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